查询CD4067BMS供应商



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Features

- High Voltage Types (20V Rating)
- CD4067BMS Single 16 Channel Multiplexer/Demultiplexer
- CD4097BMS Differential 8 Channel Multiplexer/Demultiplexer
- Low ON Resistance: 125Ω (typ) Over 15Vp-p Signal Input Range for VDD - VSS = 15V
- High OFF Resistance: Channel Leakage of ±10pA (typ) at VDD - VSS = 18V
- Matched Switch Characteristics: RON = 5Ω (typ) for VDD VSS = 15V
- Very Low Quiescent Power Dissipation Under All Digital Control Input and Supply Conditions: $0.2\mu W$ (typ) at VDD VSS = 10V
- Binary Address Decoding on Chip
- 5V, 10V and 15V Parametric Ratings
- 100% Tested for Quiescent Current at 20V
- Maximum Input Current of 1μA at 18V Over Full Package Temperature Range; 100nA at 18V and +25°C
- Standardized Symmetrical Output Characteristics

Applications

- Analog and Digital Multiplexing and Demultiplexing
- A/D and D/A Conversion
- Signal Gating
- * When these devices are used as demultiplexers the "CHANNEL IN/OUT" terminals are the outputs and the "COMMON OUT/IN" terminals are the inputs.

Description

CD4067BMS and CD4097BMS CMOS analog multiplexers/ demultiplexers* are digitally controlled analog switches having low ON Impedance, low OFF leakage current, and internal address decoding. In addition, the ON resistance is relatively constant over the full input-signal range.

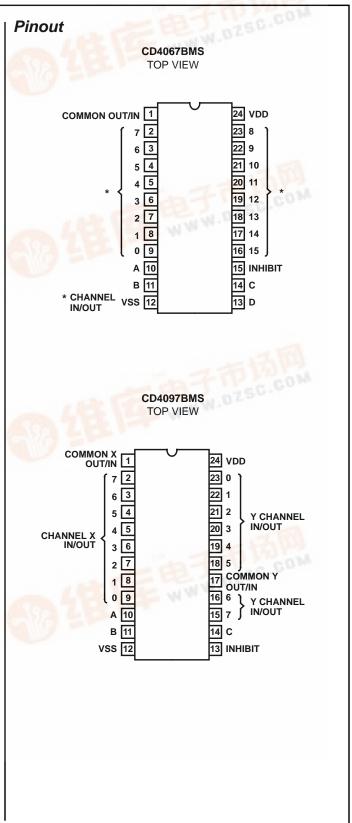
The CD4067BMS is a 16 channel multiplexer with four binary control inputs, A, B, C, D and an inhibit input, arranged so that any combination of the inputs selects one switch.

The CD4097BMS is a differential 8 channel multiplexer having three binary control inputs A, B, C and an inhibit input. The inputs permit selection of one of eight pairs of switches. A logic "1" present at the inhibit input turns all channels off.

The CD4067BMS and CD4097BMS are supplied in these 24 lead outline packages:

Braze Seal DIP	*H4V	†H6M
Frit Seal DIP	*H1Z	†HFN
Caramic Flatpack	*H4P	†H4P
*0D4067B Only	†CD4097	Έ
If dree com		

CMOS Analog Multiplexers/Demultiplexers



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ITION: These devices are consitive to electrostatic discharge: follow proper IC Handling Procedure

_____ 040

Absolute Maximum Ratings
DC Supply Voltage Range, (VDD)
Input Voltage Range, All Inputs0.5V to VDD +0.5V
DC Input Current, Any One Input±10mA
Operating Temperature Range55°C to +125°C Package Types D, F, K, H
Storage Temperature Range (TSTG)65°C to +150°C
Lead Temperature (During Soldering)+265°C
At Distance 1/16 \pm 1/32 Inch (1.59mm \pm 0.79mm) from case for 10s Maximum

Reliability Information

5		
Thermal Resistance	θ_{ia}	θ_{ic}
Ceramic DIP and FRIT Package	80°C/W	20°Ć/W
Flatpack Package	70°C/W	20°C/W
Maximum Package Power Dissipation (PD) at +125°C	
For TA = -55°C to +100°C (Package Ty	oe D, F, K)	500mW
For TA = +100°C to +125°C (Package T	ype D, F, K)	Derate
Linear	ity at 12mW/	^o C to 200mW
Device Dissipation per Output Transistor .		100mW
For TA = Full Package Temperature Rai	nge (All Pack	kage Types)
has all an Tanana and tana		47500

Junction Temperature+175°C

				GROUP A		LIMITS		
PARAMETER	SYMBOL		NOTE 1)	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VD	D or GND	1	+25°C	-	10	μA
				2	+125°C	-	1000	μA
		VDD = 18V, VIN = VD	D or GND	3	-55°C	-	10	μA
Input Leakage Current	IIL	VIN = VDD or GND	VDD = 20	1	+25°C	-100	-	nA
				2	+125°C	-1000	-	nA
			VDD = 18V	3	-55°C	-100	-	nA
Input Leakage Current	ΠΗ	VIN = VDD or GND	VDD = 20	1	+25°C	-	100	nA
				2	+125°C	-	1000	nA
			VDD = 18V	3	-55°C	-	100	nA
ON-State Resistance	RON	VDD = 5V	-	1	+25°C	-	1050	Ω
RL = 10K Returned to VDD - VSS/2		VIS = VSS to VDD		2	+125°C	-	1300	Ω
VDD - V33/2				3	-55°C	-	800	Ω
		VDD = 10V		1	+25°C	-	400	Ω
		VIS = VSS to VDD	2	+125°C	-	500	Ω	
				3	-55°C	-	310	Ω
		VDD = 15V		1	+25°C	-	240	Ω
		VIS = VSS to VDD	2	+125°C	-	320	Ω	
				3	-55°C	-	220	Ω
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10)μA	1	+25°C	-2.8	-0.7	V
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10µ.	A	1	+25°C	0.7	2.8	V
Functional (Note 4)	F	VDD = 2.8V, VIN = VI	DD or GND	7	+25°C	VOH>	VOL <	V
		VDD = 20V, VIN = VD	D or GND	7	+25°C	VDD/2	VDD/2	
		VDD = 18V, VIN = VD	D or GND	8A	+125°C			
		VDD = 3V, VIN = VDD	D or GND	8B	-55°C	1		
Input Voltage Low (Note 2)	VIL	VDD = 5V = VIS Thru VEE = VSS	1K	1, 2, 3	+25°C, +125°C, -55°C	-	1.5	V
Input Voltage High (Note 2)	VIH	RL = 1K to VSS ISS < 2μA on all OFF Channels		1, 2, 3	+25°C, +125°C, -55°C	3.5	-	V
Input Voltage Low (Note 2)	VIL	VDD = 15V = VIS Thr VEE = VSS	u 1K	1, 2, 3	+25°C, +125°C, -55°C	-	4	V
Input Voltage High (Note 2)	VIH	RL = 1K to VSS ISS < 2μA on all OFF Channels		1, 2, 3	+25°C, +125°C, -55°C	11	-	V

				GROUP A			IITS	
PARAMETER	SYMBOL		NOTE 1)	SUBGROUPS	TEMPERATURE	MIN	MAX	
OFF Channel Leakage	IOZL	VOUT = 0V	VDD = 20V	1	+25°C	-0.1	-	μA
Any Channel OFF or All Channels OFF				2	+125°C	-1.0	-	μA
(Common OUT/IN)			VDD = 18V	3	-55°C	-0.1	-	μA
	IOZH	VOUT = VDD	VDD = 20V	1	+25°C	-	0.1	μA
				2	+125°C	-	1.0	μA
			VDD = 18V	3	-55°C	-	0.1	μA

implemented.

2. Go/No Go test with limits applied to inputs.

is 0.050V max.

4. VDD = 2.8/3.0V, RL = 200K

VDD = 20V/18V, RL = 10K - 25K

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

			GROUP A		LIM		
PARAMETER	SYMBOL	CONDITIONS	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
Propagation Delay		VDD = 5V, VIN = VDD or GND	9	+25°C	-	60	ns
(Signal In to Output)	Signal In to Output) TPLH (No		10, 11	+125°C, -55°C	-	81	ns
Propagation Delay	TPZH	VDD = 5V, VIN = VDD or GND	9	+25°C	-	650	ns
Address or Inhibit to Signal Out. (Channel Turning On)	TPZL	(Notes 2, 3)	10, 11	+125°C, -55°C	-	878	ns

NOTES:

1. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

2. -55°C and +125°C limits guaranteed, 100% testing being implemented.

3. CL = 50pF, RL = 10K, Input TR, TF < 20ns.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

						LIN	IITS	
PARAMETER	SYMBOL	CONDITION	s	NOTES	TEMPERATURE	MIN	MAX	
Supply Current	IDD	VDD = 5V, VIN = VDD	or GND	1, 2	-55°C, +25°C	-	5	μΑ
					+125°C	-	150	μΑ
		VDD = 10V, VIN = VD	D or GND	1, 2	-55°C, +25°C	-	10	μΑ
					+125°C	-	300	μΑ
		VDD = 15V, VIN = VD	D or GND	1, 2	-55°C, +25°C	-	10	μΑ
					+125°C	-	600	μΑ
Input Voltage Low	VIL	VDD = VIS = 10V VEE = VSS		1, 2	+25°C, +125°C, -55°C	-	3	V
Input Voltage High	VIH	RL = 1K to VSS IIS < 2μΑ ON OFF Channel	Γ	1, 2	+25°C, +125°C, -55°C	+7	-	V
Propagation Delay	TPZH	VDD = 10V		1, 2, 4	+25°C	-	270	ns
Address or Inhibit to Signal Out. (Channel Turning On)	TPZL	VDD = 15V		1, 2, 4	+25°C	-	190	ns
Propagation Delay	TPHL		/DD or	1, 2, 3	+25°C	-	30	ns
Signal In to Output	TPLH	VDD = 15V GND		1, 2, 3	+25°C	-	20	ns

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)							
					LIM	IITS	
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Propagation Delay	TPHZ	VDD = 5V	1, 2, 5	+25°C	-	440	ns
Address or Inhibit to Signal Out	TPLZ	VDD = 10V	1, 2, 5	+25°C	-	180	ns
(Channel Turning Off)		VDD = 15V	1, 2, 5	+25°C	-	130	ns
Input Capacitance	CIN	Any Address or Inhibit	1, 2	+25°C	-	7.5	pF

NOTES:

1. All voltages referenced to device GND.

2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.

3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

4. CL = 50pF, RL = 10K, Input TR, TF < 20ns.

5. CL = 50pF, RL = 300Ω , Input TR, TF < 20ns.

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

					LIM	IITS	
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1, 4	+25°C	-	25	μA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10μA	1, 4	+25°C	-2.8	-0.2	V
N Threshold Voltage Delta	ΔVTN	VDD = 10V, ISS = -10µA	1, 4	+25°C	-	±1	V
P Threshold Voltage	VTP	VSS = 0V, IDD = 10µA	1, 4	+25°C	0.2	2.8	V
P Threshold Voltage Delta	ΔVTP	VSS = 0V, IDD = 10µA	1, 4	+25°C	-	±1	V
Functional	F	VDD = 18V, VIN = VDD or GND	1	+25°C	VOH >	VOL <	V
		VDD = 3V, VIN = VDD or GND			VDD/2	VDD/2	
Propagation Delay Time	TPHL TPLH	VDD = 5V	1, 2, 3, 4	+25°C	-	1.35 x +25⁰C Limit	ns

NOTES: 1. All voltages referenced to device GND.

3. See Table 2 for +25°C limit.

2. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

4. Read and Record

TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS +25°C

PARAMETER	SYMBOL	DELTA LIMIT
Supply Current - MSI-2	IDD	± 1.0μA
ON Resistance	RONDEL10	± 20% x Pre-Test Reading

TABLE 6. APPLICABLE SUBGROUPS

CONFORMANCE GROUP	MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Initial Test (Pre Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A, RONDEL10
Interim Test 1 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A, RONDEL10
Interim Test 2 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A, RONDEL10
PDA (Note 1)	100% 5004	1, 7, 9, Deltas	
Interim Test 3 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A, RONDEL10
PDA (Note 1)	100% 5004	1, 7, 9, Deltas	
Final Test	100% 5004	2, 3, 8A, 8B, 10, 11	

TABLE 6. APPLICABLE SUBGROUPS							
CONFORMANCE GROUP		MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD			
Group A		Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11				
Group B	Subgroup B-5	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas	Subgroups 1, 2, 3, 9, 10, 11			
	Subgroup B-6	Sample 5005	1, 7, 9				
Group D		Sample 5005	1, 2, 3, 8A, 8B, 9	Subgroups 1, 2 3			

NOTE: 1.5% Parameteric, 3% Functional; Cumulative for Static 1 and 2.

TABLE 7. TOTAL DOSE IRRADIATION

	MIL-STD-883	TE	TEST		READ AND RECORD	
CONFORMANCE GROUPS	METHOD	PRE-IRRAD	POST-IRRAD	PRE-IRRAD	POST-IRRAD	
Group E Subgroup 2	5005	1, 7, 9	Table 4	1, 9	Table 4	

TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

FUNCTION	OPEN	GROUND	VDD	9V ± -0.5V	OSCILLATOR	
					50kHz	25kHz
PART NUMBER CD4067E	BMS				•	
Static Burn-In 1 Note 1	1	2 - 23	24			
Static Burn-In 2 Note 1	1	12	2 - 11, 13 - 24			
Dynamic Burn-In Note 1	-	12, 15	24	1	2 - 9, 16 - 23	10, 11, 13, 14 (Note 3)
Irradiation Note 2	1	12	2 - 11, 13 - 24			
PART NUMBER CD4097E	BMS	•			•	
Static Burn-In 1 Note 1	1, 17	2 - 16, 18 - 23	24			
Static Burn-In 2 Note 1	1, 17	12	2 - 11, 13 - 16, 18 - 24			
Dynamic Burn-In Note 1	-	12, 13	24	1, 17	2 - 9, 15, 16, 18 - 23	10, 11, 14 (Note 4)
Irradiation Note 2	1, 17	12	2 - 11, 13 - 16, 18 - 24			

NOTE:

1. Each pin except VDD and GND will have a series resistor of 10K \pm 5%, VDD = 18V \pm 0.5V

2. Each pin except VDD and GND will have a series resistor of 47K \pm 5%; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures, VDD = 10V \pm 0.5V

3. Pin 10 is at 14kHz, Pin 11 is at 7kHz, Pin 13 is at 1.7kHz, Pin 14 is at 3.5kHz

4. Pin 10 is at 14kHz, Pin 11 is at 7kHz, Pin 14 is at 3.5kHZ

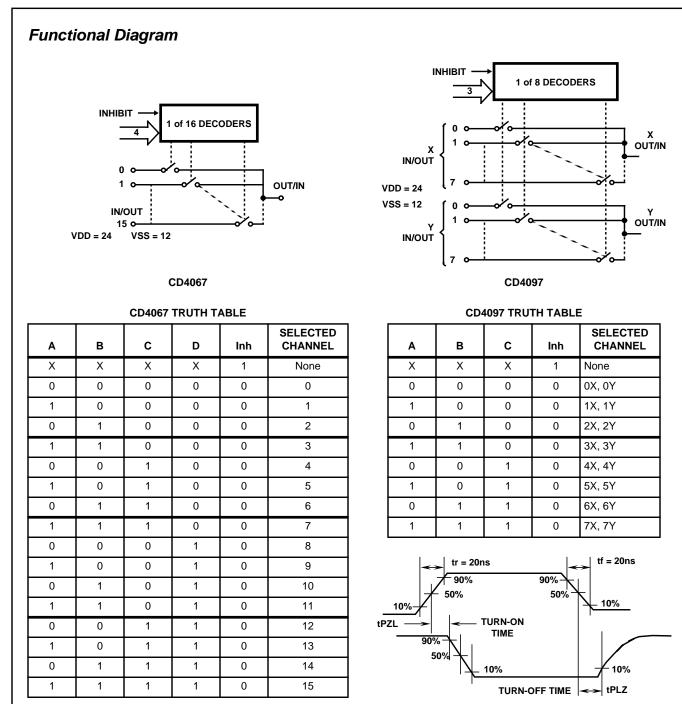


FIGURE 1. WAVEFORM CHANNEL BEING TURNED ON, OFF

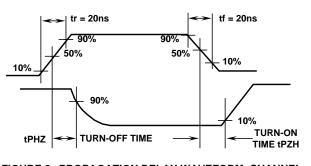
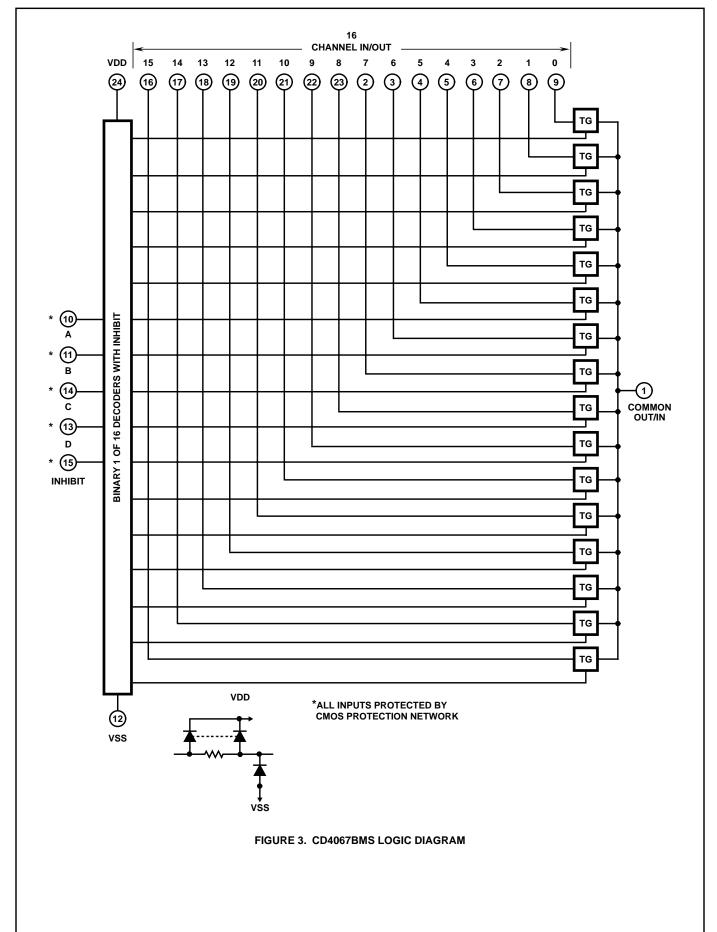
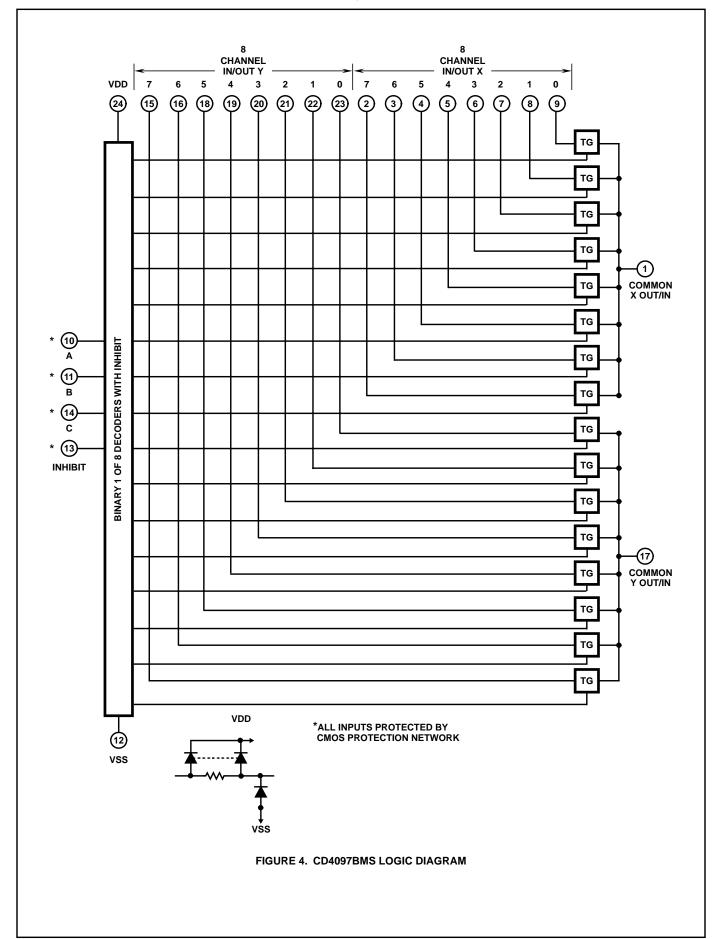


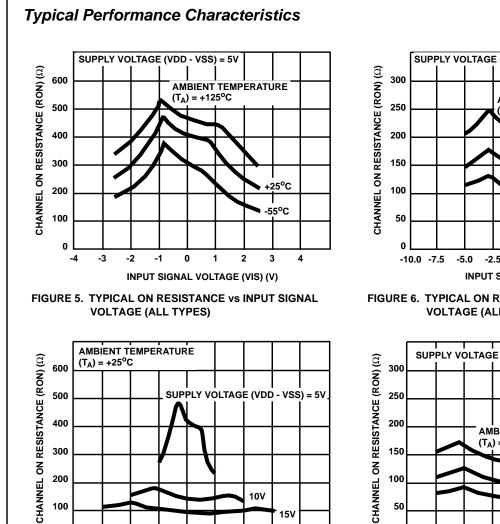
FIGURE 2. PROPAGATION DELAY WAVEFORM, CHANNEL BEING TURNED OFF, ON

CD4067BMS, CD4097BMS



CD4067BMS, CD4097BMS





15V

10.0

7.5

5.0

INPUT SIGNAL VOLTAGE (VIS) (V) FIGURE 7. TYPICAL ON RESISTANCE vs INPUT SIGNAL **VOLTAGE (ALL TYPES)**

0

2.5

-2.5

100

0

-10.0 -7.5

-5.0

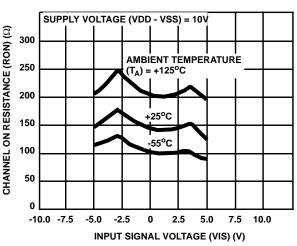


FIGURE 6. TYPICAL ON RESISTANCE vs INPUT SIGNAL **VOLTAGE (ALL TYPES)**

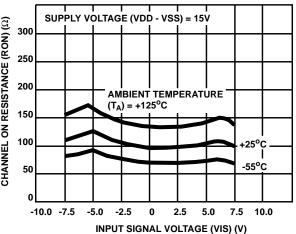
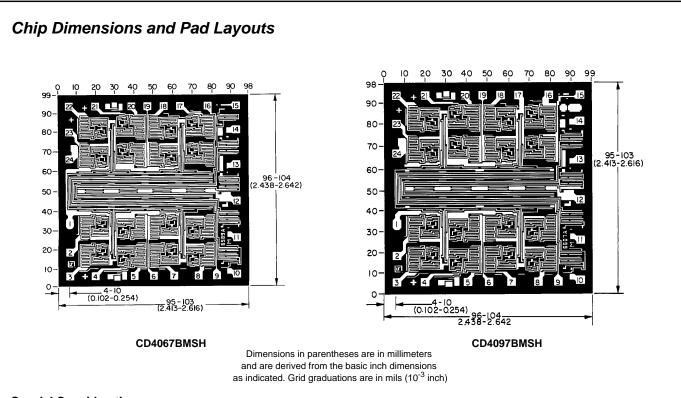


FIGURE 8. TYPICAL ON RESISTANCE vs INPUT SIGNAL **VOLTAGE (ALL TYPES)**



Special Considerations

In applications where separate power sources are used to drive VDD and the signal inputs, the VDD current capability should exceed VDD/RL (RL = effective external load). This provision avoids permanent current flow or clamp action on the VDD supply when power is applied or removed from the CD4067BMS or CD4097BMS.

When switching from one address to another, some of the ON periods of the channels of the multiplexers will overlap momentarily, which may be objectionable in certain applications. Also when a channel is turned on or off by an address input, there is a momentary conductive path from the channel to VSS, which will dump some charge from any capacitor connected to the input or output of the channel. The inhibit input turning on a channel will similarly dump some charge to VSS.

The amount of charge dumped is mostly a function of the signal level above VSS. Typically, at VDD - VSS = 10V, a 100pF capacitor connected to the input or output of the

channel will lose 3 to 4% of its voltage at the moment the channel turns on or off. This loss of voltage is essentially independent of the address or inhibit signal transition time, if the transition time is less than 1 - 2μ s. When the inhibit signal turns a channel off, there is no charge dumping to VSS. Rather, there is a slight rise in the channel voltage level (65mV typ.) due to capacitive coupling from inhibit input to channel input or output. Address inputs also couple some voltage steps onto the channel signal levels.

In certain applications, the external load resistor current may include both VDD and signal-line components. To avoid drawing VDD current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0.8 volt (calculated from RON values shown in ELECTRICAL CHARACTERISTICS CHART - Table 1). no VDD current will flow through RL if the switch current flows into terminal 1 on the CD4067BMS, terminals 1 and 17 on the CD4097BMS.

METALLIZATION: Thickness: 11kÅ – 14kÅ, AL. PASSIVATION: 10.4kÅ - 15.6kÅ, Silane BOND PADS: 0.004 inches X 0.004 inches MIN DIE THICKNESS: 0.0198 inches - 0.0218 inches

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